

SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

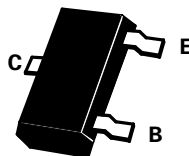
FMMTA55 FMMTA56

ISSUE 3 – JANUARY 1996 

FEATURES

* Gain of 50 at $I_C=100\text{mA}$

PARTMARKING DETAIL - FMMTA55 - 2H
FMMTA56 - 2G
FMMTA55R - NB
FMMTA56R - MB



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA55	FMMTA56	UNIT
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4		V
Continuous Collector Current	I_C	-500		mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	330		mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	FMMTA55		FMMTA56		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60		-80		V	$I_C=-1\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4		-4		V	$I_E=-100\mu\text{A}, I_C=0$
Collector-Emitter Cut-Off Current	I_{CES}		-0.1		-0.1	μA	$V_{CE}=-60\text{V}$
Collector-Base Cut-Off Current	I_{CBO}		-0.1		-0.1	μA	$V_{CB}=-80\text{V}, I_E=0$ $V_{CB}=-60\text{V}, I_E=0$
Static Forward Current Transfer Ratio	h_{FE}	50 50		50 50			$I_C=-10\text{mA}, V_{CE}=1\text{V}^*$ $I_C=-100\text{mA}, V_{CE}=1\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25		-0.25	V	$I_C=-100\text{mA}, I_B=-10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2		-1.2	V	$I_C=-100\text{mA}, V_{CE}=-1\text{V}^*$
Transition Frequency	f_T	100		100		MHz	$I_C=-10\text{mA}, V_{CE}=-2\text{V}$ $f=100\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$